



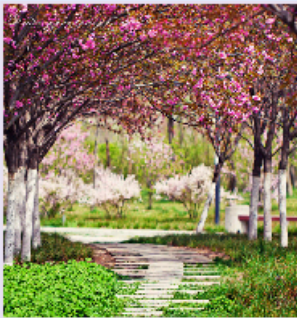
科学研究

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科研论文(杂志与国际会议)-2012年

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